

# **Device Modeling Report**

COMPONENTS:  
DIODE/ SCHOTTKY RECTIFIER / STANDARD  
PART NUMBER: XBS306S17R  
MANUFACTURER: TOREX SEMICONDUCTOR

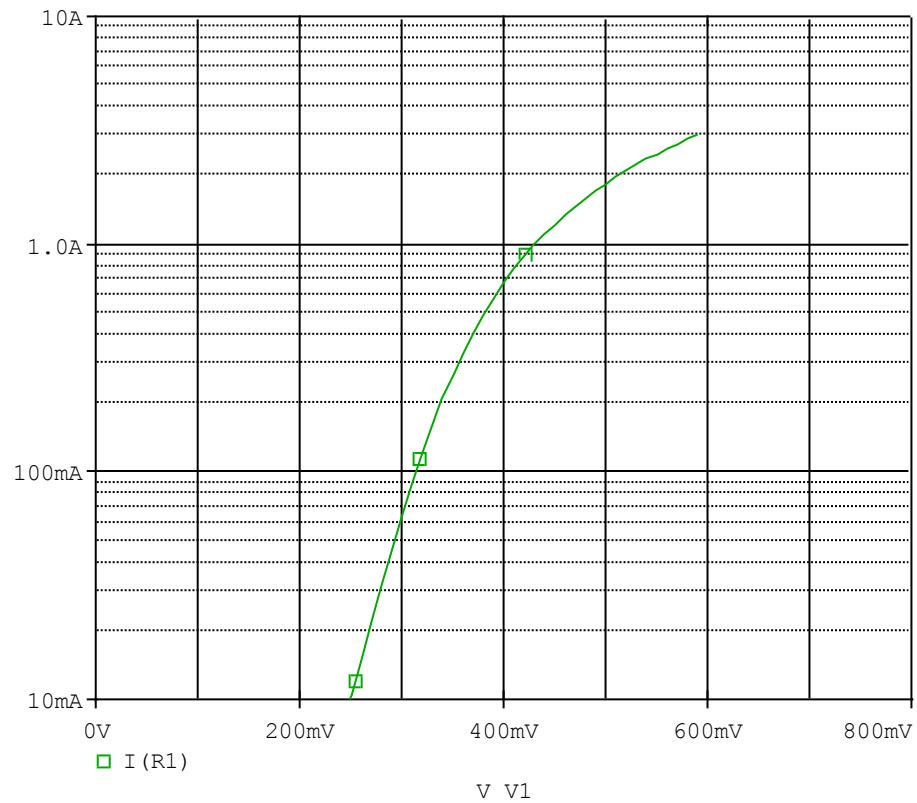


**Bee Technologies Inc.**

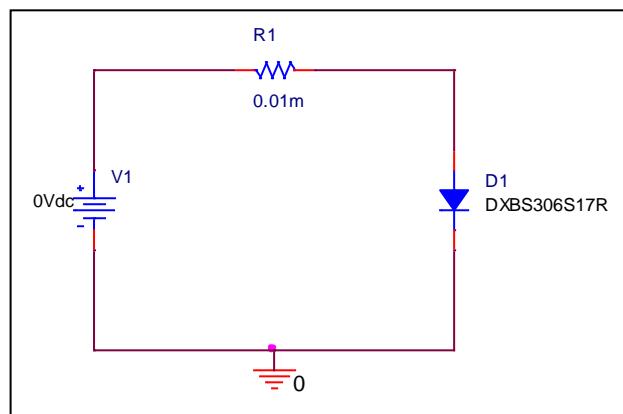
PSpice model parameter	Model description
IS	Saturation Current
N	Emission Coefficient
RS	Series Resistance
IKF	High-injection Knee Current
CJO	Zero-bias Junction Capacitance
M	Junction Grading Coefficient
VJ	Junction Potential
ISR	Recombination Current Saturation Value
BV	Reverse Breakdown Voltage(a positive value)
IBV	Reverse Breakdown Current(a positive value)
TT	Transit Time
EG	Energy-band Gap

## Forward Current Characteristic

Circuit Simulation Result

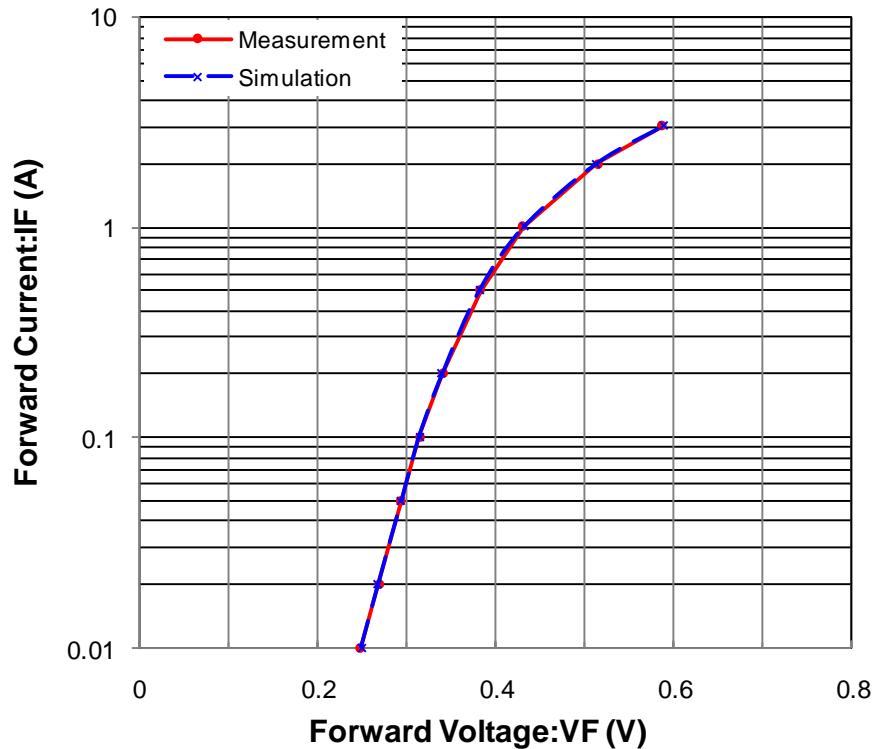


Evaluation Circuit



## Comparison Graph

Circuit Simulation Result

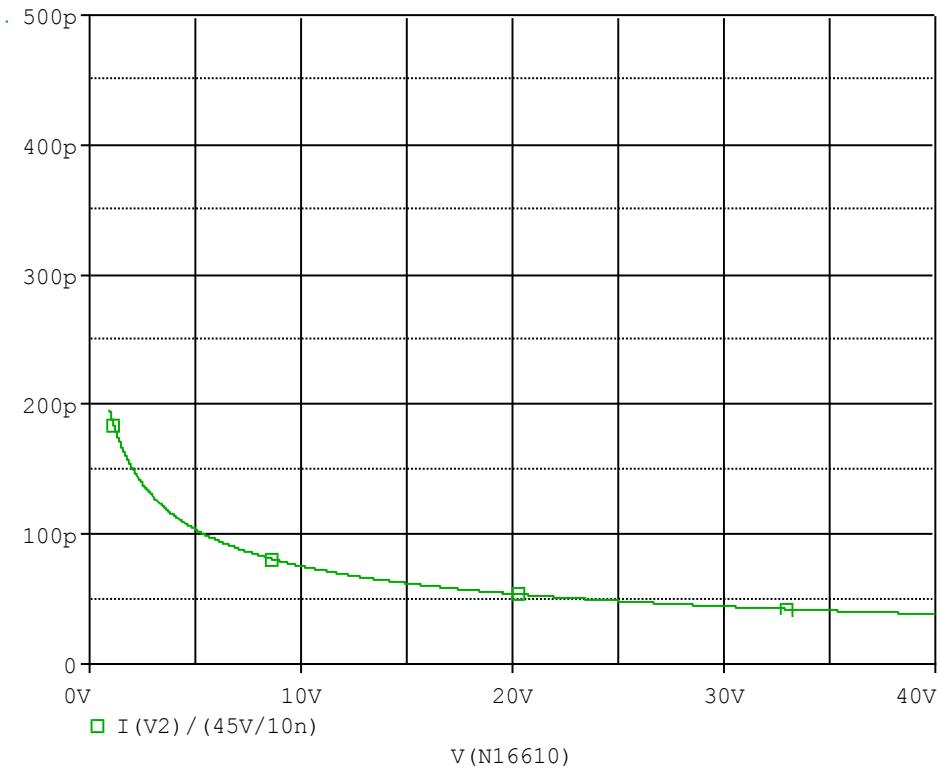


Simulation Result

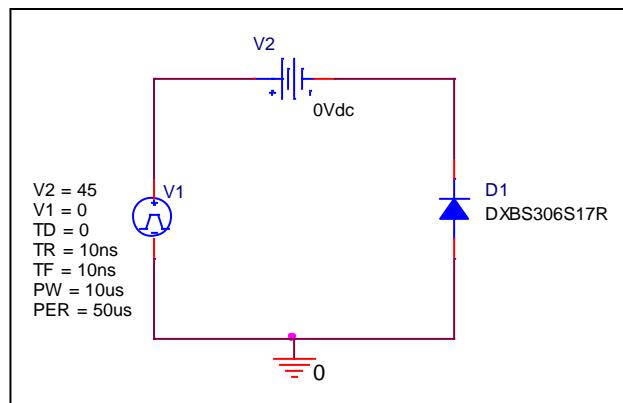
$I_F$ (A)	$V_F$ (V)		%Error
	Measurement	Simulation	
0.01	0.248	0.249	0.55
0.02	0.268	0.267	-0.27
0.05	0.293	0.293	-0.04
0.1	0.314	0.314	0.01
0.2	0.340	0.339	-0.43
0.5	0.382	0.381	-0.15
1	0.430	0.431	0.30
2	0.514	0.513	-0.18
3	0.587	0.587	0.06

## Capacitance Characteristic

### Circuit Simulation Result

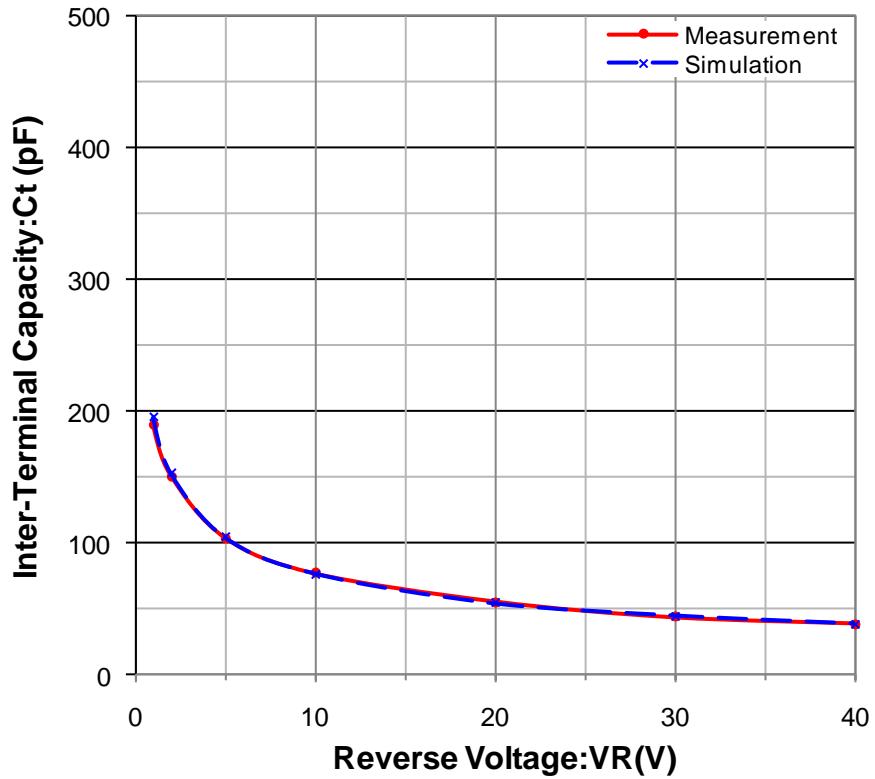


### Evaluation Circuit



## Comparison Graph

Circuit Simulation Result

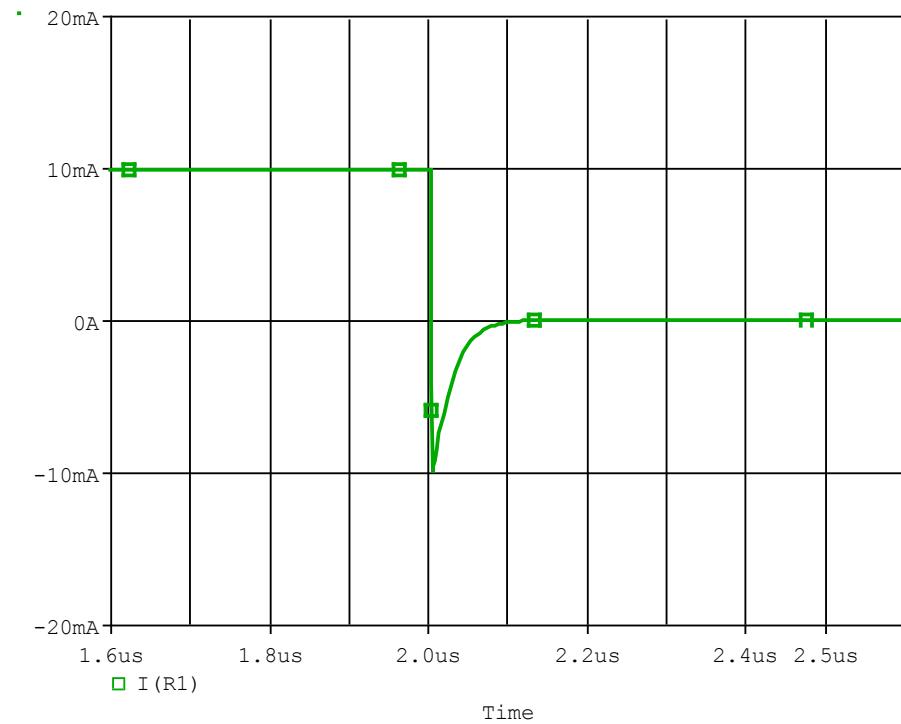


Simulation Result

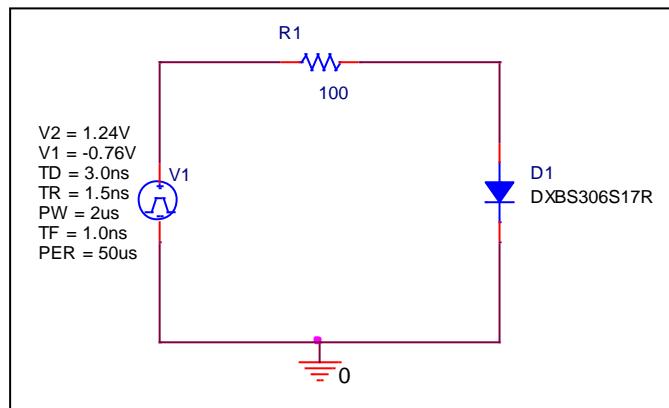
$V_R$ (V)	Ct (pF)		%Error
	Measurement	Simulation	
1	189.000	195.271	3.32
2	150.000	152.893	1.93
5	103.000	104.254	1.22
10	77.000	75.723	-1.66
20	55.000	54.162	-1.52
30	43.575	44.419	1.94
40	38.000	38.464	1.22

## Reverse Recovery Characteristic

### Circuit Simulation Result



### Evaluation Circuit



Compare Measurement vs. Simulation

Parameter	Unit	Measurement	Simulation	%Error
trr	ns	55.000	56.083	1.97